T-46-23-12

P4C116/P4C116L
ULTRA HIGH SPEED 2K x 8
STATIC CMOS RAMS (SCRAMS)

FEATURES

- Full CMOS, 6T Cell
- High Speed (Equal Access and Cycle Times)
  - 15/20/25/35 ns (Commercial)
  - 20/25/35/45 ns (Military)
- Low Power Operation (Commercial/Military)
  - 605/715 mW Active — 15, 20
  - 485/575 mW Active — 25, 35, 45
  - 116/127 mW Standby (TTL Input)
  - 1.1 mW Standby (CMOS Input) P4C116L
- Output Enable Control Function
- Single 5V±10% Power Supply
- Data Retention with 2.0V Supply, 10 µA Typical Current
- Common Data I/O
- Fully TTL Compatible Inputs and Outputs
- Produced with PACE II Technology™
- Standard Pinout (JEDEC Approved)
  - 24-Pin 300 mil DIP, SOIC

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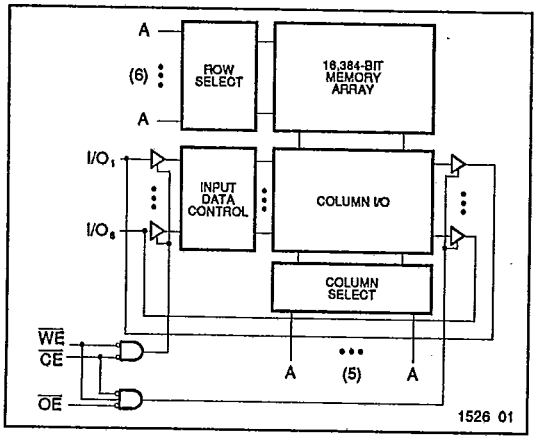
DESCRIPTION

The P4C116 and P4C116L are 16,384-bit ultra high-speed static RAMs organized as 2K x 8. The CMOS memories require no clocks or refreshing and have equal access and cycle times. Inputs are fully TTL-compatible. The RAMs operate from a single 5V±10% tolerance power supply. With battery backup, data integrity is maintained for supply voltages down to 2.0V. Current drain is typically 10 µA from a 2.0V supply.

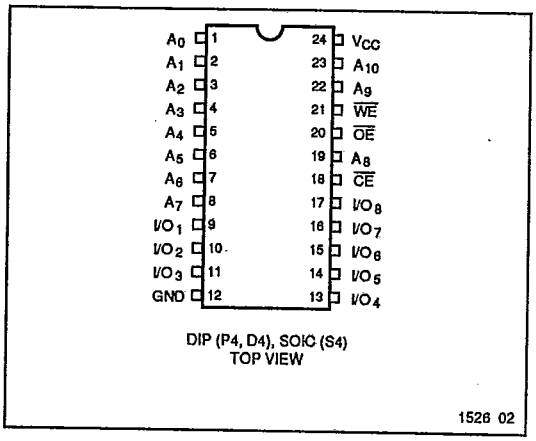
Access times as fast as 15 nanoseconds are available, permitting greatly enhanced system operating speeds. CMOS is utilized to reduce power consumption to a low 605 mW active, 116 mW standby. In full standby mode with CMOS inputs, power comsumption is only 1.1 mW for the P4C116L. The P4C116 and P4C116L are members of a family of PACE RAM™ products offering super fast access times never before available at these complexity levels in TTL-compatible bipolar or CMOS technologies. The P4C116 and P4C116L are manufactured with PACE II Technology™.

The P4C116 and P4C116L are available in 24-pin 300 mil DIP and SOIC packages providing excellent board level densities.

FUNCTIONAL BLOCK DIAGRAM



PIN CONFIGURATIONS



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MAXIMUM RATINGS[1]

Symbol	Parameter	Value	Unit
V_{CC}	Power Supply Pin with Respect to GND	–0.5 to +7	V
V_{TERM}	Terminal Voltage with Respect to GND (up to 7.0V)	–0.5 to V_{CC} +0.5	V
T_A	Operating Temperature	–55 to +125	°C

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Symbol	Parameter	Value	Unit
T_{BIAS}	Temperature Under Bias	–55 to +125	°C
T_{STG}	Storage Temperature	–65 to +150	°C
P_T	Power Dissipation	1.0	W
I_{OUT}	DC Output Current	50	mA

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RECOMMENDED OPERATING TEMPERATURE AND SUPPLY VOLTAGE

Grade[2]	Ambient Temperature	GND	V_{CC}
Military	–55 to +125°C	0V	5.0V ± 10%

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Grade[2]	Ambient Temperature	GND	V_{CC}
Commercial	0°C to +70°C	0V	5.0V ± 10%

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DC ELECTRICAL CHARACTERISTICS

Over recommended operating temperature and supply voltage[2]

Symbol	Parameter	Test Conditions		P4C116		P4C116L		Unit
				Min	Max	Min	Max	
V_{IH}	Input High Voltage			2.2	V_{CC}+0.5	2.2	V_{CC}+0.5	V
V_{IL}	Input Low Voltage			–0.5[3]	0.8	–0.5[3]	0.8	V
V_{HC}	CMOS Input High Voltage			V_{CC}–0.2	V_{CC}+0.5	V_{CC}–0.2	V_{CC}+0.5	V
V_{LC}	CMOS Input Low Voltage			–0.5[3]	0.2	–0.5[3]	0.2	V
V_{CD}	Input Clamp Diode Voltage	V_{CC} = Min., I_{IN} = –18 mA			–1.2		–1.2	V
V_{OL}	Output Low Voltage (TTL Load)	I_{OL} = +10 mA, V_{CC} = Min. I_{OL} = +8 mA, V_{CC} = Min.			0.5 0.4		0.5 0.4	V
V_{OLC}	Output Low Voltage (CMOS Load)	I_{OLC} = +100 µA, V_{CC} = Min.			0.2		0.2	V
V_{OH}	Output High Voltage (TTL Load)	I_{OH} = –4 mA, V_{CC} = Min.		2.4		2.4		V
V_{OHC}	Output High Voltage (CMOS Load)	I_{OHC} = –100 µA, V_{CC} = Min.		V_{CC}–0.2		V_{CC}–0.2		V
I_{LI}	Input Leakage Current	V_{CC} = Max. V_{IN} = GND to V_{CC}	Mil. Com'l.	–10 –5	+10 +5	–5 –2	+5 +2	µA
I_{LO}	Output Leakage Current	V_{CC} = Max., $\overline{CE}$ = V_{IH}, V_{OUT} = GND to V_{CC}	Mil. Com'l.	–10 –5	+10 +5	–5 –2	+5 +2	µA

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CAPACITANCES[4]

(V_{CC} = 5.0V, T_A = 25°C, f = 1.0MHz)

Symbol	Parameter	Conditions	Typ.	Unit
C_{IN}	Input Capacitance	V_{IN} = 0V	5	pF

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Symbol	Parameter	Conditions	Typ.	Unit
C_{OUT}	Output Capacitance	V_{OUT} = 0V	7	pF

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Notes:

1. Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to MAXIMUM rating conditions for extended periods may affect reliability.
2. Extended temperature operation guaranteed with 400 linear feet per minute of air flow.
3. Transient inputs with V_{IL} and I_{IL} not more negative than –3.0V and –100mA, respectively, are permissible for pulse widths up to 20 ns.
4. This parameter is sampled and not 100% tested.

POWER DISSIPATION CHARACTERISTICS

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Over recommended operating temperature and supply voltage[2]

Symbol	Parameter	Test Conditions		P4C116 Min	P4C116 Max	P4C116L Min	P4C116L Max	Unit
I_{CC}	Dynamic Operating Current – 15, 20	V_{CC} = Max., f = Max., Outputs Open	Mil.	—	130	—	130	mA
			Com'l.	—	110	—	110	
I_{CC}	Dynamic Operating Current – 25, 35, 45	V_{CC} = Max., f = Max., Outputs Open	Mil.	—	105	—	105	mA
			Com'l.	—	90	—	90	
I_{SB}	Standby Power Supply Current (TTL Input Levels)	$\overline{CE} \geq V_{IH}$, V_{CC} = Max., f = Max., Outputs Open	Mil.	—	23	—	23	mA
			Com'l.	—	21	—	21	
I_{SB1}	Standby Power Supply Current (CMOS Input Levels)	$\overline{CE} \geq V_{HC}$, V_{CC} = Max., f = 0, Outputs Open, $V_{IN} \leq V_{LC}$ or $V_{IN} \geq V_{HC}$	Mil.	—	18	—	1	mA
			Com'l.	—	17	—	0.2	

n/a = Not Applicable

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DATA RETENTION CHARACTERISTICS (P4C116L Only)

Symbol	Parameter	Test Condition	Min	Typ.* V_{CC}= 2.0V	Typ.* V_{CC}= 3.0V	Max V_{CC}= 2.0V	Max V_{CC}= 3.0V	Unit
V_{DR}	V_{CC} for Data Retention		2.0					V
I_{CCDR}	Data Retention Current	Mil.		10	15	200	300	µA
		Com'l.		10	15	60	90	µA
t_{CDR}	Chip Deselect to Data Retention Time	$\overline{CE} \geq V_{CC} - 0.2V$, $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$	0					ns
t_R†	Operation Recovery Time		t_{RC}§					ns

*T_A = +25°C

§t_{RC} = Read Cycle Time

†This parameter is guaranteed but not tested.

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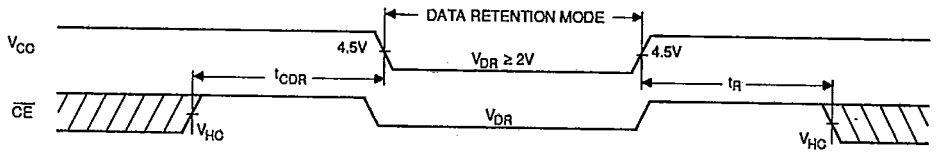
DATA RETENTION WAVEFORM



1526 03

AC ELECTRICAL CHARACTERISTICS—READ CYCLE

(V_{CC} = 5V ± 10%, All Temperature Ranges)[2]

Sym.	Parameter	-15*		-20		-25		-35		-45		Unit
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
t_{RC}	Read Cycle Time	15		20		25		35		45		ns
t_{AA}	Address Access Time		15		20		25		35		45	ns
t_{AC}	Chip Enable Access Time		15		20		25		35		45	ns
t_{OH}	Output Hold from Address Change	2		2		3		3		3		ns
t_{LZ}	Chip Enable to Output in Low Z	2		2		3		3		3		ns
t_{HZ}	Chip Disable to Output in High Z		7		8		10		15		20	ns
t_{OE}	Output Enable Low to Data Valid		10		10		15		20		25	ns
t_{OLZ}	Output Enable Low to Low Z	0		0		0		0		0		ns
t_{OHZ}	Output Enable High to High Z		8		9		12		15		15	ns
t_{PU}	Chip Enable to Power Up Time	0		0		0		0		0		ns
t_{PD}	Chip Disable to Power Down		20		20		20		20		25	ns

*V_{CC} = 5V ± 5% for -15

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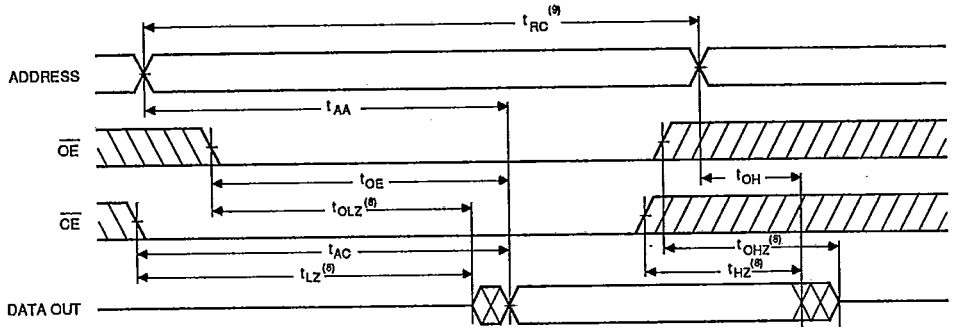
TIMING WAVEFORM OF READ CYCLE NO. 1 ($\overline{OE}$ CONTROLLED) [5]



1526 04

Notes:
5. $\overline{WE}$ is high for READ cycle.
6. $\overline{CE}$ is low and $\overline{OE}$ is low for READ cycle.
7. ADDRESS must be valid prior to, or coincident with $\overline{CE}$ transition low.
8. Transition is measured ± 200 mV from steady state voltage prior to change, with loading as specified in Figure 1. This parameter is sampled and not 100% tested.

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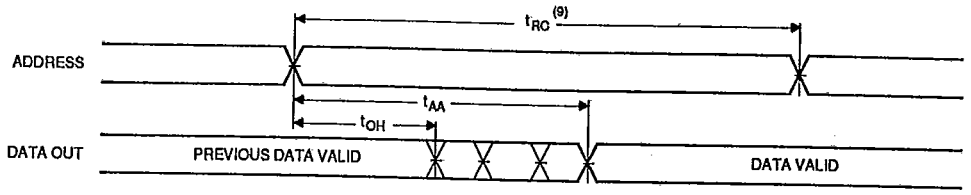
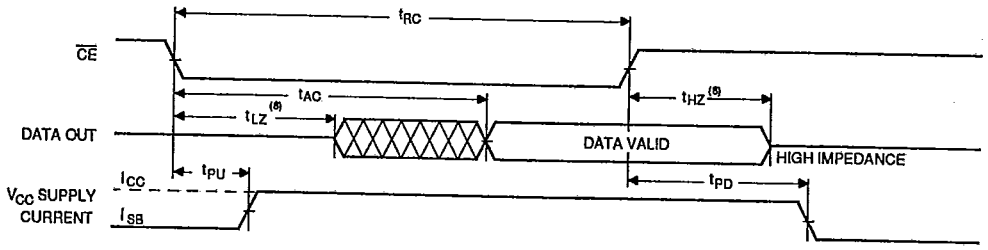
TIMING WAVEFORM OF READ CYCLE NO. 2 (ADDRESS CONTROLLED) [5,6]



1526 05

TIMING WAVEFORM OF READ CYCLE NO. 3 ($\overline{CE}$ CONTROLLED) [5,7]



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Notes:

9. READ Cycle Time is measured from the last valid address to the first transitioning address.

2

AC CHARACTERISTICS—WRITE CYCLE

(V_{CC} = 5V ± 10%, All Temperature Ranges)[2]

Sym.	Parameter	-15*		-20		-25		-35		-45		Unit
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
t_{WC}	Write Cycle Time	15		20		25		35		45		ns
t_{CW}	Chip Enable Time to End of Write	12		15		18		25		30		ns
t_{AW}	Address Valid to End of Write	12		15		18		25		30		ns
t_{AS}	Address Set-up Time	0		0		0		0		0		ns
t_{WP}	Write Pulse Width	12		15		18		20		20		ns
t_{AH}	Address Hold Time	0		0		0		0		0		ns
t_{WR}	Write Recovery Time	0		0		0		0		0		ns
t_{DW}	Data Valid to End of Write	10		12		15		20		20		ns
t_{DH}	Data Hold Time	0		0		0		0		0		ns
t_{WZ}	Write Enable to Output in High Z		7		8		10		15		15	ns
t_{OW}	Output Active from End of Write	0		0		0		0		0		ns

*V_{CC} = 5V ± 5% for -15

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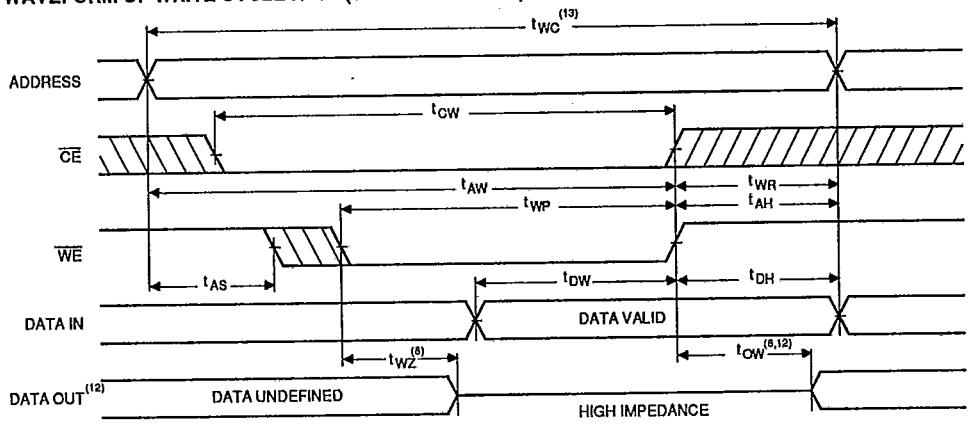
TIMING WAVEFORM OF WRITE CYCLE NO. 1 ($\overline{WE}$ CONTROLLED) [10]



1526 07

Notes:

10. $\overline{CE}$ and $\overline{WE}$ must be low for WRITE cycle.
11. $\overline{OE}$ is low for this WRITE cycle to show t_{WZ} and t_{OW}.
12. If $\overline{CE}$ goes high simultaneously with $\overline{WE}$ high, the output remains in a low impedance state
13. Write Cycle Time is measured from the last valid address to the first transitioning address.

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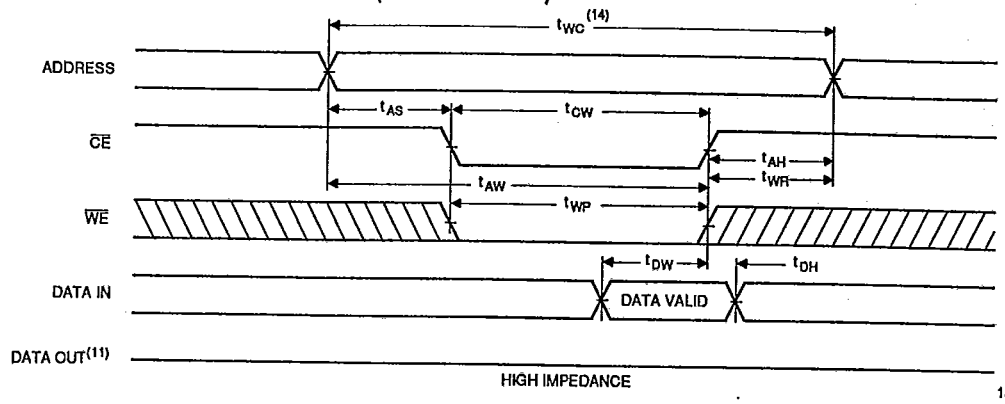
TIMING WAVEFORM OF WRITE CYCLE NO. 2 ($\overline{CE}$ CONTROLLED) (11)



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2

AC TEST CONDITIONS

Input Pulse Levels	GND to 3.0V
Input Rise and Fall Times	3ns
Input Timing Reference Level	1.5V
Output Timing Reference Level	1.5V
Output Load	See Figures 1 and 2

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TRUTH TABLE

Mode	$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	I/O	Power
Standby	H	X	X	High Z	Standby
D_{OUT} Disabled	L	H	H	High Z	Active
Read	L	L	H	D_{OUT}	Active
Write	L	X	L	High Z	Active

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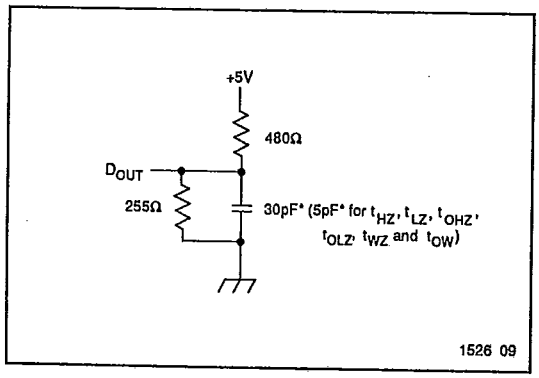

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Figure 1. Output Load

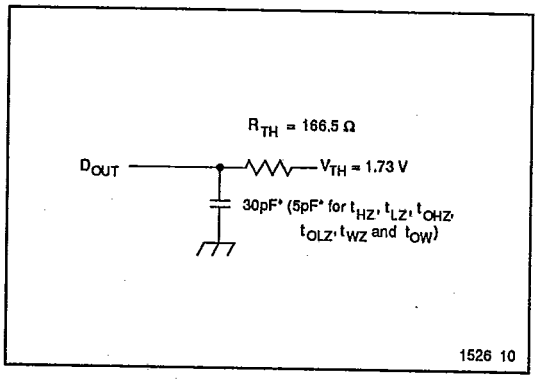

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Figure 2. Thevenin Equivalent

* including scope and test fixture.

Note:
Due to the ultra-high speed of the P4C116/L, care must be taken when testing this device; an inadequate setup can cause a normal functioning part to be rejected as faulty. Long high-inductance leads that cause supply bounce must be avoided by bringing the V_{cc} and ground planes directly up to the contactor fingers. A 0.01 µF high frequency capacitor is also required between V_{cc} and ground. To avoid signal reflections, proper termination must be used; for example, a 50Ω test environment should be terminated into a 50Ω load with 1.73V (Thevenin Voltage) at the comparator input, and a 116Ω resistor must be used in series with D_{OUT} to match 166Ω (Thevenin Resistance).

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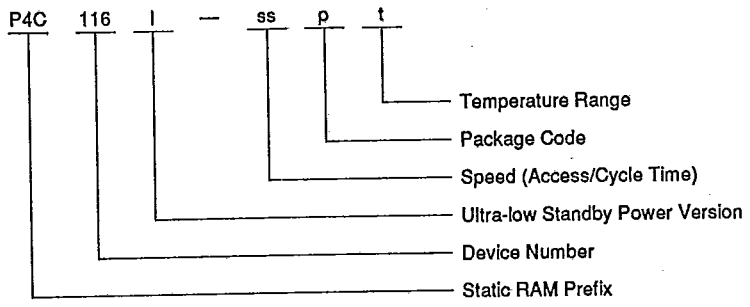
ORDERING INFORMATION



l = Ultra-low standby power designator L, if needed.
ss = Speed (access/cycle time in ns), e.g., 15, 20
p = Package code, i.e., P, S, D.
t = Temperature range, i.e., C, M, MB.

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PACKAGE SUFFIX

Package Suffix	Description
P	Plastic DIP, 300 mil wide standard
S	Plastic SOIC, 300 mil wide standard
D	CERDIP, 300 mil wide standard

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TEMPERATURE RANGE SUFFIX

Temperature Range Suffix	Description
C	Commercial Temperature Range, 0°C – +70°C.
M	Military Temperature Range, –55°C – +125°C.
MB	Mil. Temp. with MIL-STD-883C Class B compliance

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SELECTION GUIDE

The P4C116/L is available in the following temperature, speed and package options.

Temp. Range	Speed (ns) / Package	15	20	25	35	45
Com'l	Plastic DIP	-15PC	-20PC	-25PC	-35PC	N/A
	Plastic SOIC	-15SC	-20SC	-25SC	-35SC	N/A
	CERDIP	-15DC	-20DC	-25DC	-35DC	N/A
Mil. Temp.	CERDIP	N/A	-20DM	-25DM	-35DM	-45DM
Military Proc'd*	CERDIP	N/A	-20DMB	-25DMB	-35DMB	-45DMB

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* Military temperature range with MIL-STD-883 Revision C, Class B processing.
N/A = Not available

TECHDOC 1526